

Micro Commercial Components 20736 Marilla Street Chatsworth

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MMSS8050

Features

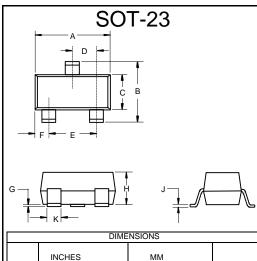
- SOT-23 Plastic-Encapsulate Transistors
- Capable of 0.625Watts(Tamb=25°C) of Power Dissipation.
- Collector-current 1.5A
- Collector-base Voltage 40V
- Operating and storage junction temperature range: -55°C to +150°C
- Marking Code: Y1

NPN Silicon Plastic-Encapsulate Transistor

Electrical Characteristics @ 25°C Unless Otherwise Specified

Symbol	Parameter	Min	Max	Units
OFF CHARAC	CTERISTICS			
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	40		Vdc
, , , , , ,	(b=100uAdc, l _E =0)			
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	25		Vdc
	(b=0.1mAdc, l _B =0)			
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	5.0		Vdc
	(½=100uAdc, l _C =0)			
Сво	Collector Cutoff Current		0.1	uAdc
	(V _{CB} =40Vdc, <u></u> =0)			
PEO	Collector Cutoff Current		0.1	uAdc
	(V _{CE} =20Vdc, _b =0)			
I EBO	Emitter Cutoff Current		0.1	uAdc
	(V _{EB} =5.0Vdc, <i>\</i> c=0)			
ON CHARAC	TERISTICS			
h _{FE(1)}	DC Current Gain	120	350	
	(b=100mAdc, V _{CE} =1.0Vdc)			
h _{FE(2)}	DC Current Gain	40		
	(b=800mAdc, Vce=1.0Vdc)			
V _{CE(sat)}	Collector-Emitter Saturation Voltage		0.5	Vdc
	(b=800mAdc, l _B =80mAdc)			
$V_{BE(sat)}$	Base-Emitter Saturation Voltage		1.2	Vdc
. ,	(b=800mAdc, l _B =80mAdc)			
V_{EB}	Base- Emitter Voltage		1.6	Vdc
	(I _E =1.5Adc)			
SMALL-SIGN	IAL CHARACTERISTICS			
f _T	Transistor Frequency	100		MHz
	(L=50mAdc, V _{CE} =10Vdc, f=30MHz)		1	

CLASSIFICATION OF H _{E (1)}							
Rank	L	Н					
Range	120-200	200-350					



	INCHES		MM				
DIM	MIN	MAX	MIN	MAX	NOTE		
Α	.110	.120	2.80	3.04			
В	.083	.098	2.10	2.64			
O	.047	.055	1.20	1.40			
О	.035	.041	.89	1.03			
П	.070	.081	1.78	2.05			
F	.018	.024	.45	.60			
Ð	.0005	.0039	.013	.100			
I	.035	.044	.89	1.12			
J	.003	.007	.085	.180			
K	.015	.020	.37	.51			

Suggested Solder Pad Layout O31 800 O35 900 inches mm

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